



SPW52N50C3

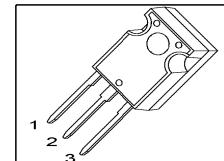
Cool MOS™ Power Transistor

Feature

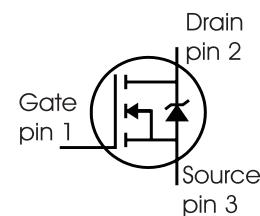
- New revolutionary high voltage technology
- Worldwide best $R_{DS(on)}$ in TO 247
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- Ultra low effective capacitances
- Improved transconductance

$V_{DS} @ T_{jmax}$	560	V
$R_{DS(on)}$	0.07	Ω
I_D	52	A

P-TO247



Type	Package	Ordering Code	Marking
SPW52N50C3	P-TO247	Q67040-S4615	52N50C3



Maximum Ratings

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25^\circ\text{C}$	I_D	52	A
$T_C = 100^\circ\text{C}$		30	
Pulsed drain current, t_p limited by T_{jmax}	$I_{D \text{ puls}}$	156	
Avalanche energy, single pulse $I_D = 10 \text{ A}, V_{DD} = 50 \text{ V}$	E_{AS}	1800	mJ
Avalanche energy, repetitive t_{AR} limited by T_{jmax} ¹ $I_D = 20 \text{ A}, V_{DD} = 50 \text{ V}$	E_{AR}	1	
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	20	A
Gate source voltage	V_{GS}	± 20	V
Gate source voltage AC ($f > 1\text{Hz}$)	V_{GS}	± 30	
Power dissipation, $T_C = 25^\circ\text{C}$	P_{tot}	417	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	°C

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain Source voltage slope $V_{DS} = 400 \text{ V}$, $I_D = 52 \text{ A}$, $T_j = 125^\circ\text{C}$	dv/dt	50	V/ns

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	-	-	0.3	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
Soldering temperature, 1.6 mm (0.063 in.) from case for 10s	T_{sold}	-	-	260	°C

Electrical Characteristics, at $T_j=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{V}$, $I_D=0.25\text{mA}$	500	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{V}$, $I_D=20\text{A}$	-	600	-	
Gate threshold voltage	$V_{GS(th)}$	$I_D=2700\mu\text{A}$, $V_{GS}=V_{DS}$	2.1	3	3.9	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=500\text{V}$, $V_{GS}=0\text{V}$, $T_j=25^\circ\text{C}$, $T_j=150^\circ\text{C}$	-	0.5	25	μA
-			-	-	250	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{V}$, $V_{DS}=0\text{V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$, $I_D=30\text{A}$, $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	-	0.06	0.07	Ω
-			-	0.16	-	
Gate input resistance	R_G	f=1MHz, open Drain	-	0.7	-	

Electrical Characteristics , at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Transconductance	g_{fs}	$V_{DS} \geq 2 * I_D * R_{DS(on)max}$, $I_D = 30\text{A}$	-	40	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	-	6800	-	pF
Output capacitance	C_{oss}		-	2200	-	
Reverse transfer capacitance	C_{rss}		-	150	-	
Effective output capacitance, ²⁾ energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V to } 400\text{V}$	-	212	-	pF
Effective output capacitance, ³⁾ time related	$C_{o(tr)}$		-	469	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 380\text{V}$, $V_{GS} = 0/10\text{V}$, $I_D = 52\text{A}$, $R_G = 1.8\Omega$	-	20	-	ns
Rise time	t_r		-	30	-	
Turn-off delay time	$t_{d(off)}$		-	120	-	
Fall time	t_f		-	10	-	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 380\text{V}$, $I_D = 52\text{A}$	-	30	-	nC
Gate to drain charge	Q_{gd}		-	160	-	
Gate charge total	Q_g	$V_{DD} = 380\text{V}$, $I_D = 52\text{A}$, $V_{GS} = 0$ to 10V	-	290	-	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 380\text{V}$, $I_D = 52\text{A}$	-	5	-	V

¹Repetitive avalanche causes additional power losses that can be calculated as $P_{AV} = E_{AR} * f$.

² $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

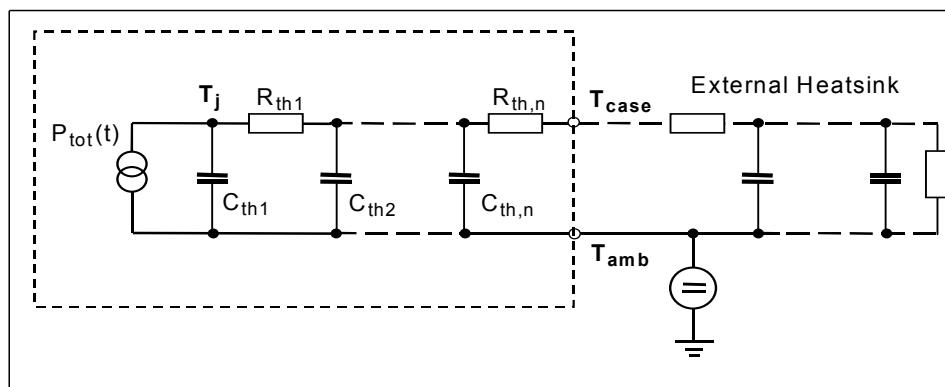
³ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	I_S	$T_C=25^\circ\text{C}$	-	-	52	A
Inverse diode direct current, pulsed	I_{SM}		-	-	156	
Inverse diode forward voltage	V_{SD}	$V_{GS}=0\text{V}$, $I_F=I_S$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R=380\text{V}$, $I_F=I_S$, $dI_F/dt=100\text{A}/\mu\text{s}$	-	580	-	ns
Reverse recovery charge	Q_{rr}		-	20	-	μC
Peak reverse recovery current	I_{rrm}		-	70	-	A
Peak rate of fall of reverse recovery current	dI_{rr}/dt		-	900	-	$\text{A}/\mu\text{s}$

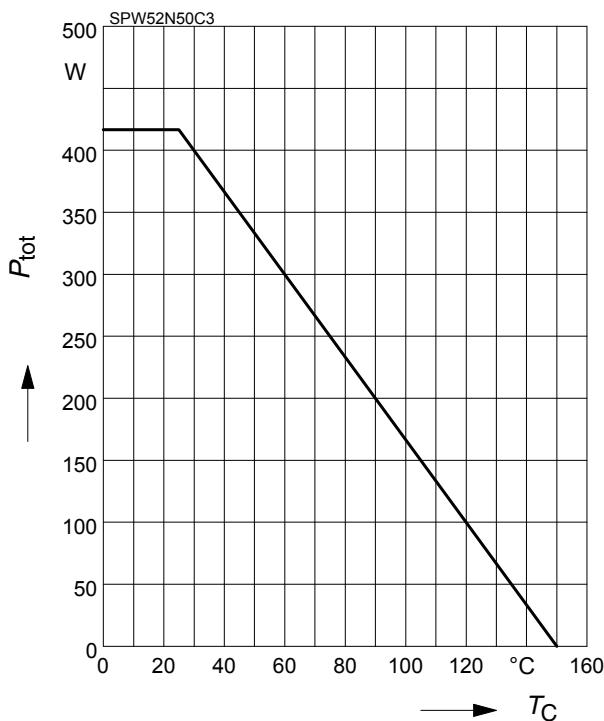
Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
Thermal resistance			Thermal capacitance		
R_{th1}	0.002689	K/W	C_{th1}	0.001081	Ws/K
R_{th2}	0.005407		C_{th2}	0.004021	
R_{th3}	0.011		C_{th3}	0.005415	
R_{th4}	0.054		C_{th4}	0.014	
R_{th5}	0.071		C_{th5}	0.025	
R_{th6}	0.036		C_{th6}	0.158	



1 Power dissipation

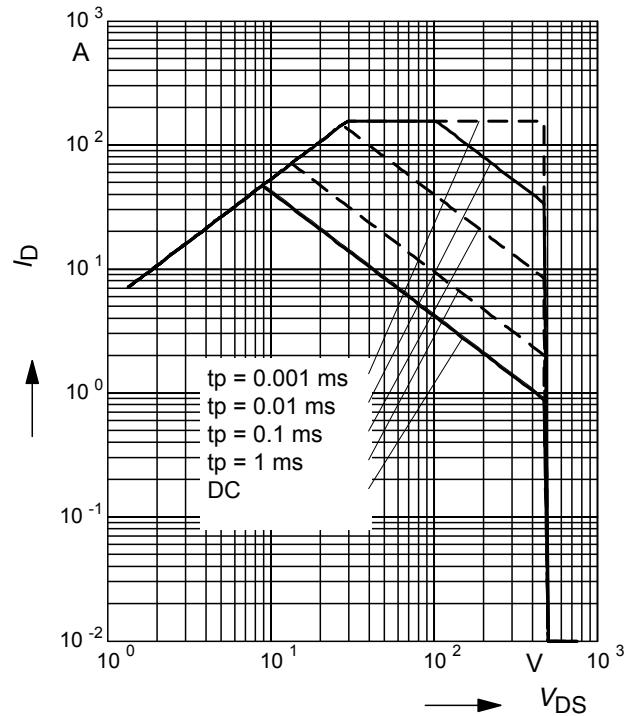
$$P_{\text{tot}} = f(T_C)$$



2 Safe operating area

$$I_D = f(V_{DS})$$

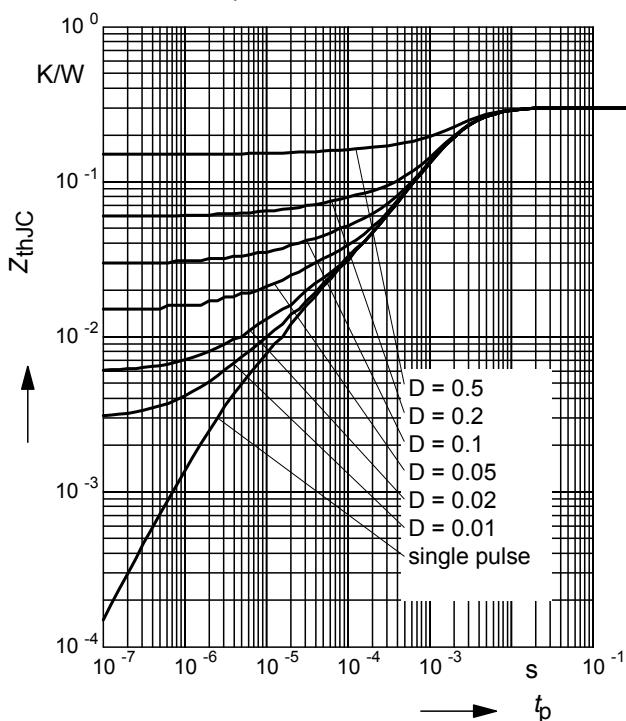
parameter : $D = 0$, $T_C = 25^\circ\text{C}$



3 Transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

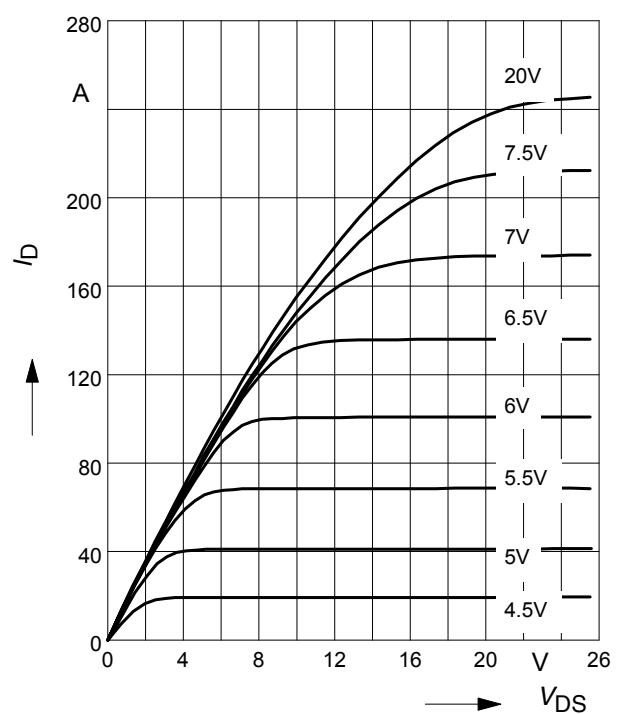
parameter: $D = t_p/T$



4 Typ. output characteristic

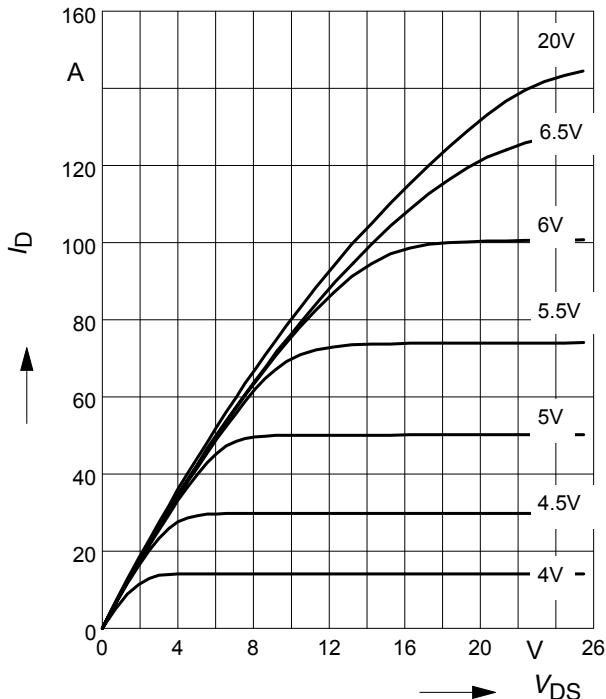
$$I_D = f(V_{DS}); \quad T_j = 25^\circ\text{C}$$

parameter: $t_p = 10 \mu\text{s}$, V_{GS}



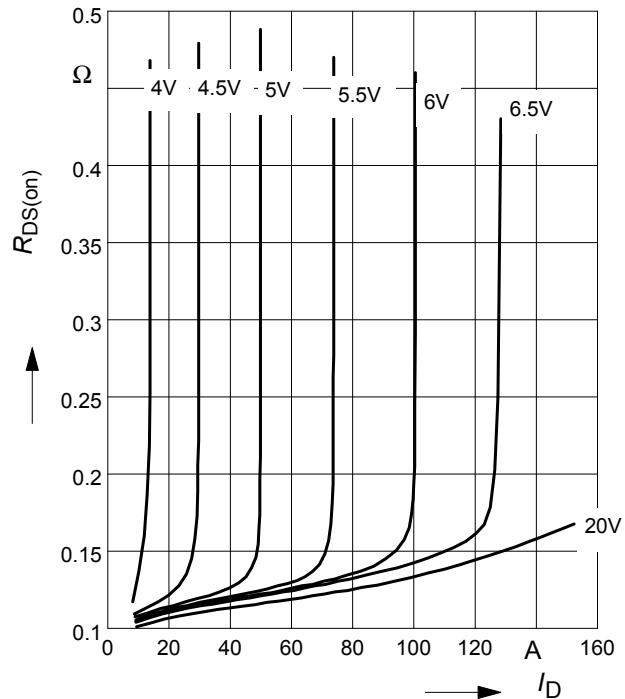
5 Typ. output characteristic

$I_D = f(V_{DS})$; $T_j=150^\circ\text{C}$
parameter: $t_p = 10 \mu\text{s}$, V_{GS}



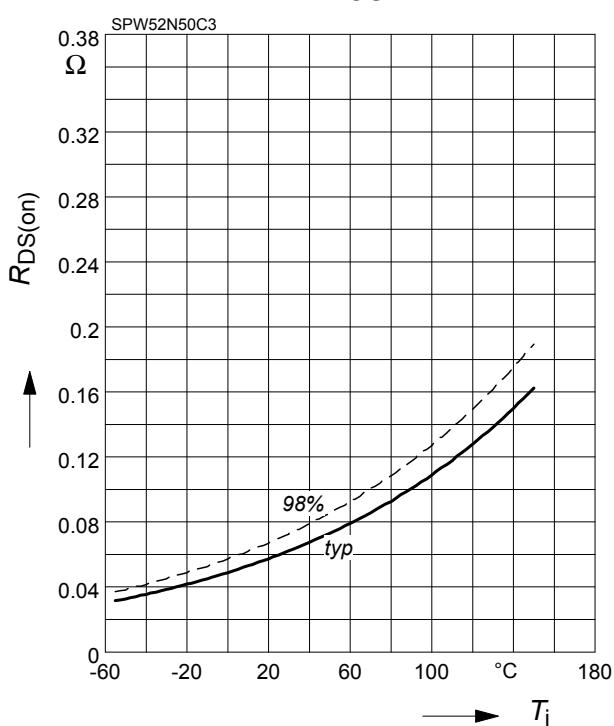
6 Typ. drain-source on resistance

$R_{DS(on)}=f(I_D)$
parameter: $T_j=150^\circ\text{C}$, V_{GS}



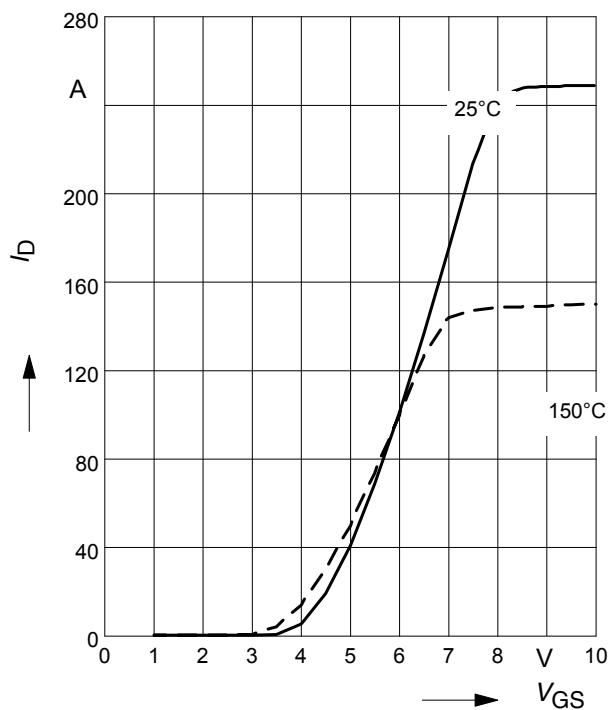
7 Drain-source on-state resistance

$R_{DS(on)}=f(T_j)$
parameter : $I_D = 30 \text{ A}$, $V_{GS} = 10 \text{ V}$



8 Typ. transfer characteristics

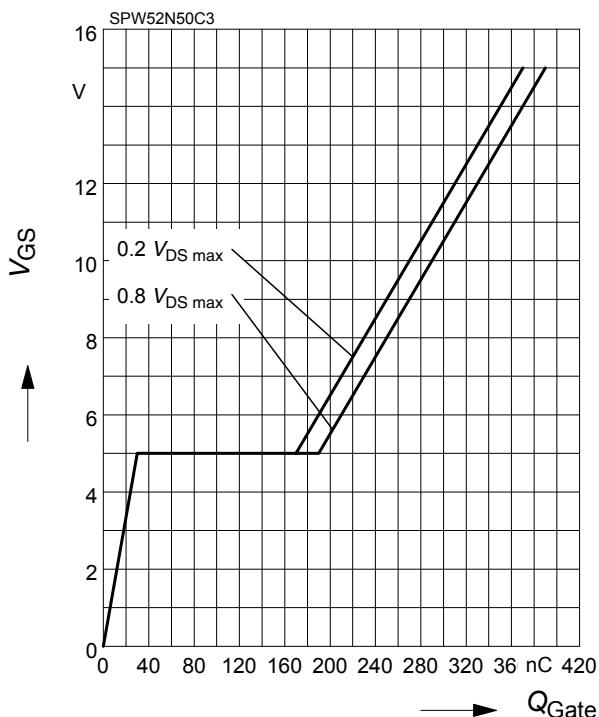
$I_D = f(V_{GS})$; $V_{DS} \geq 2 \times I_D \times R_{DS(on)\max}$
parameter: $t_p = 10 \mu\text{s}$



9 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

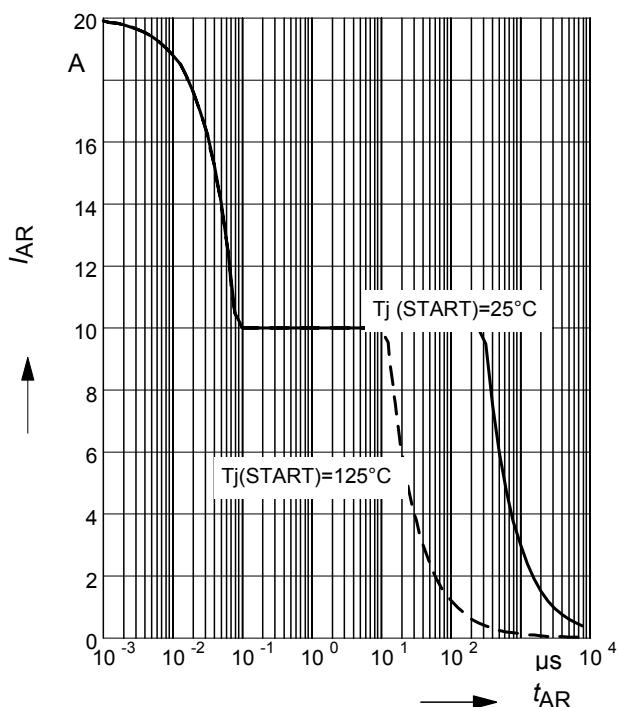
parameter: $I_D = 52 \text{ A pulsed}$



11 Avalanche SOA

$$I_{AR} = f(t_{AR})$$

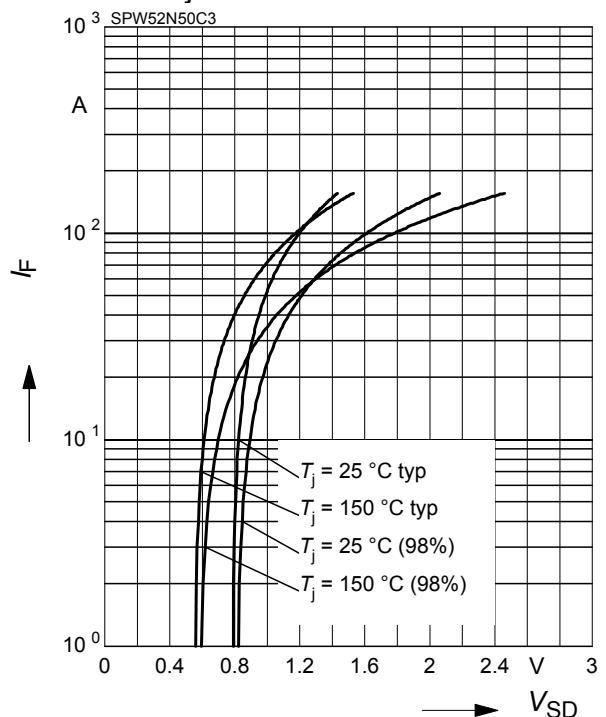
par.: $T_j \leq 150^\circ\text{C}$



10 Forward characteristics of body diode

$$I_F = f(V_{SD})$$

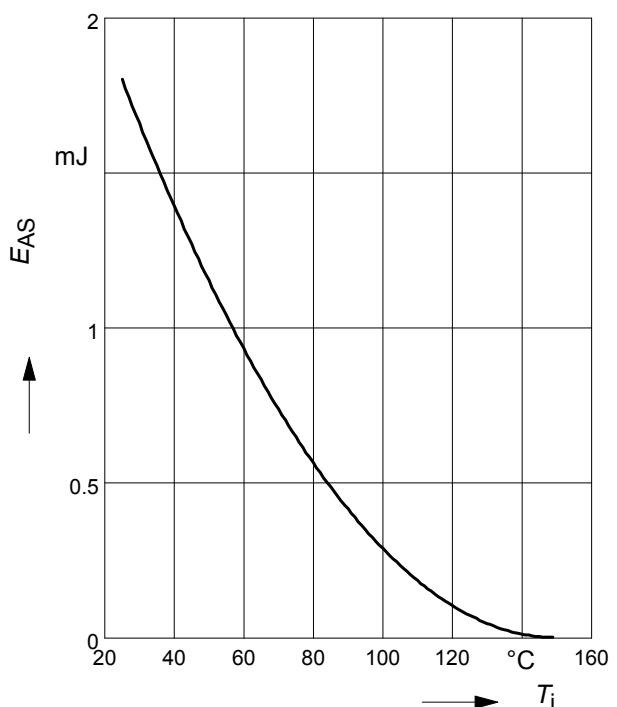
parameter: $T_j, t_p = 10 \mu\text{s}$



12 Avalanche energy

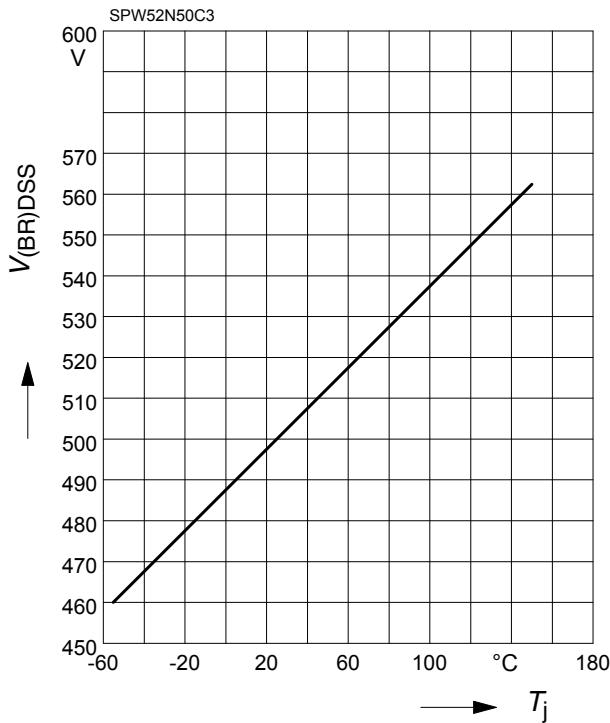
$$E_{AS} = f(T_j)$$

par.: $I_D = 10 \text{ A}, V_{DD} = 50 \text{ V}$



13 Drain-source breakdown voltage

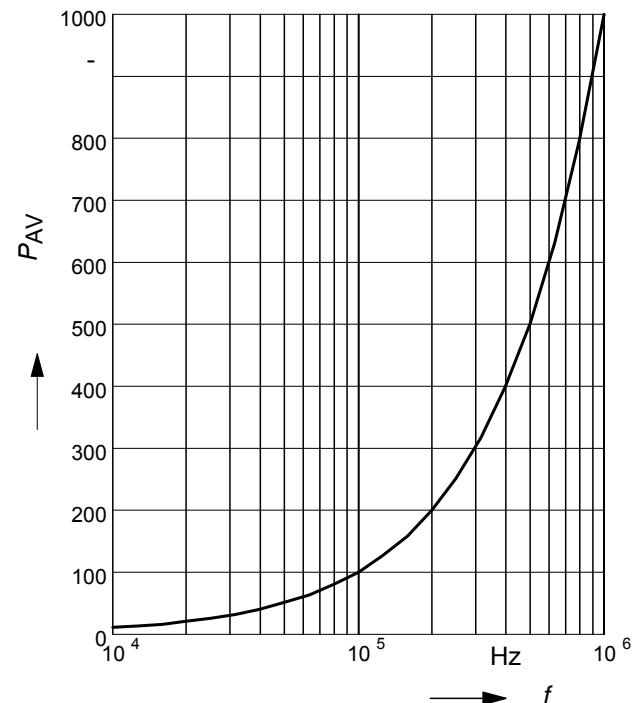
$$V_{(BR)DSS} = f(T_j)$$



14 Avalanche power losses

$$P_{AR} = f(f)$$

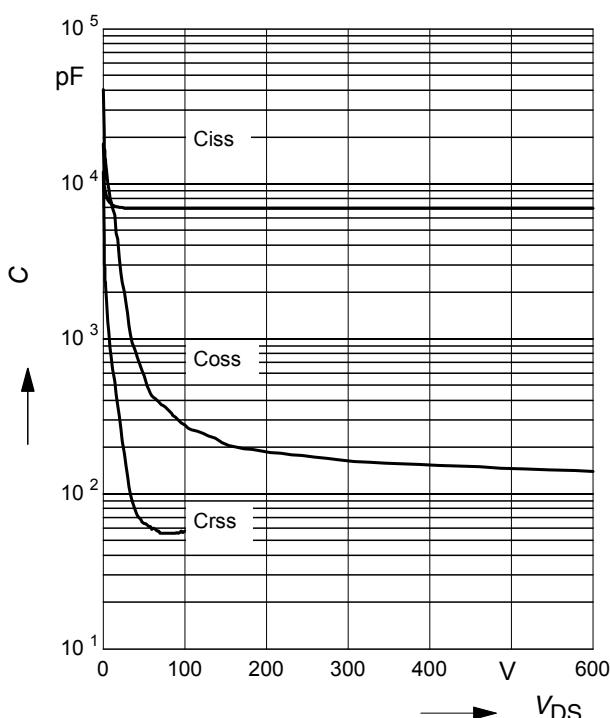
parameter: $E_{AR}=1\text{mJ}$



15 Typ. capacitances

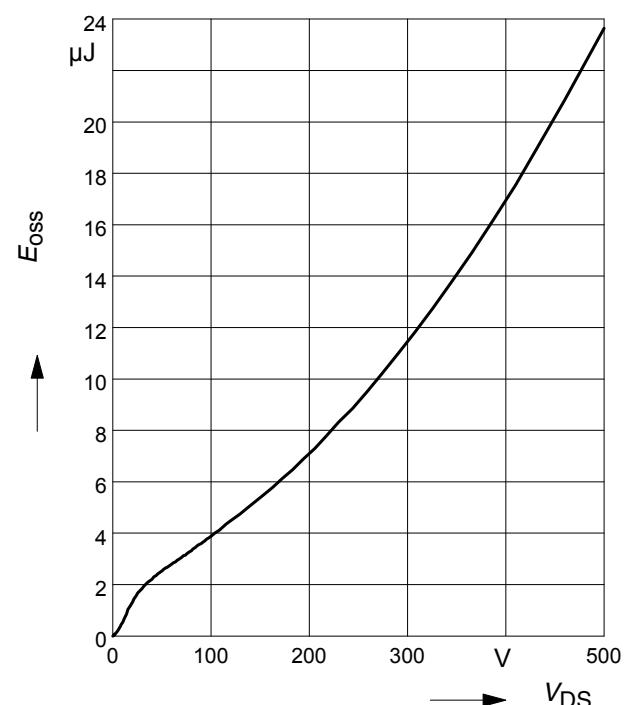
$$C = f(V_{DS})$$

parameter: $V_{GS}=0\text{V}$, $f=1\text{MHz}$

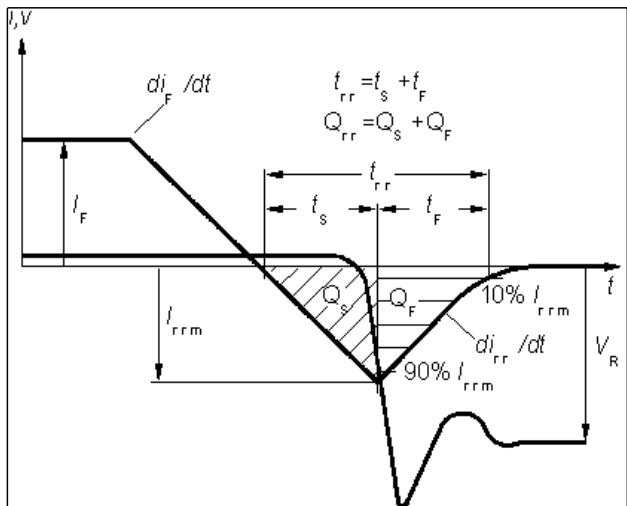


16 Typ. C_{OSS} stored energy

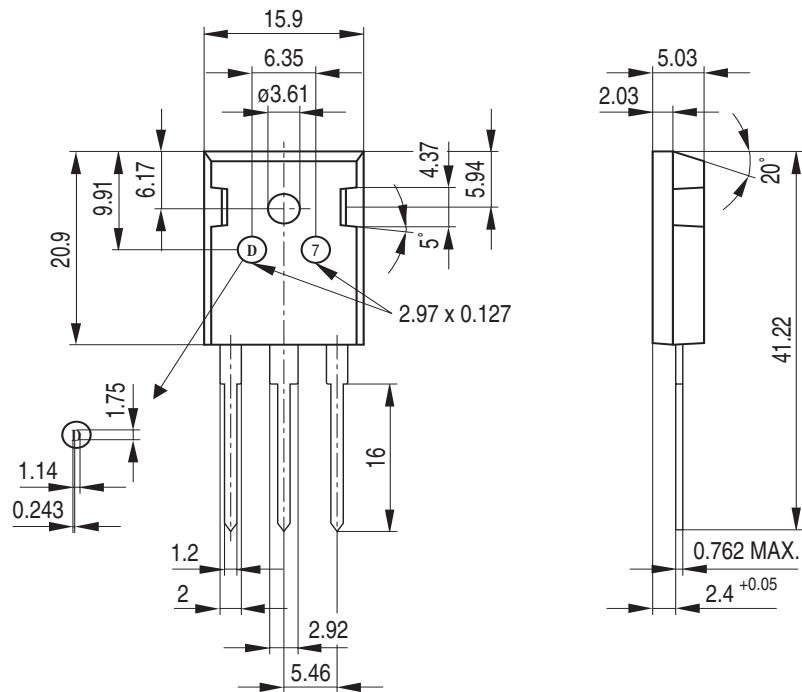
$$E_{OSS}=f(V_{DS})$$



Definition of diodes switching characteristics



P-TO-247-3-1



General tolerance unless otherwise specified: Leadframe parts: ± 0.05
Package parts: ± 0.12

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